

FEE only

May-09-05 07:56A MayerFortkort&WilliamsPC 9085187795

P.02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Richard A. Blanchard

Serial No.: 10/724,849

Filed: December 1, 2003

Title: High Voltage Power MOSFET Having A Voltage Sustaining Region That Includes Doped Columns Formed By Trench Etching and Ion Implantation

Art Unit: 2811

Examiner: Steven Ho Yin Lokc

Docket No.: GS 156 D1

Customer No.: 27774

Confirmation No. 2167

RECEIVED
CENTRAL FAX CENTER

MAY 09 2005

Via Facsimile 703-872-9306
Commissioner for Patents
PO Box 1450
Alexandria, VA 22313-1450

AMENDMENT

Sir:

In response to the (*Ex parte Quayle*) Office Action dated February 28, 2005, kindly the above-identified application as follows. In addition, any deficiencies may be charged to deposit account No. 50-1047.

05/24/2005 LWISE1 00000002 501047 10724849

01 FC:1251 120.00 DA

<p><u>Certificate of Facsimile Transmission</u> I hereby certify that this document and any document referenced herein has been transmitted via facsimile to the US Patent and Trademark Office at (703) 872-9306 on <u>May 8, 2005</u>.</p> <p><u>Karin L. Williams, Reg. No. 36,721</u> (Printed Name of Person Mailing Correspondence)</p> <p><u>Karin L. Williams</u> (Signature)</p>
